PROCESS CP191

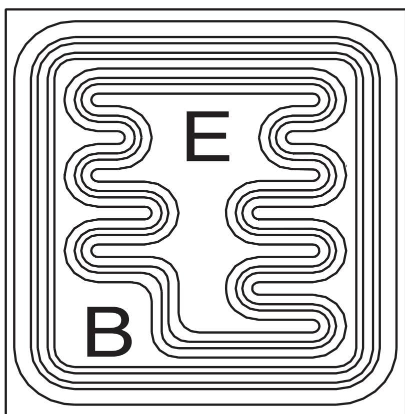
Small Signal Transistor

NPN - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16.5 x 16.5 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER
41,690

PRINCIPAL DEVICE TYPES
2N2219A
2N2222A
CMPT2222A
CMST2222A
CXT2222A
CZT2222A
MD2219A
PN2222A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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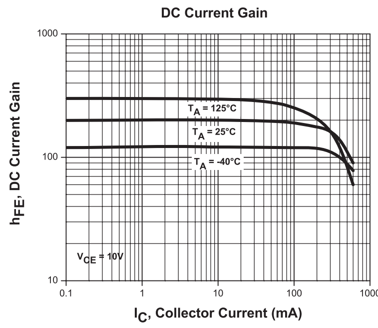
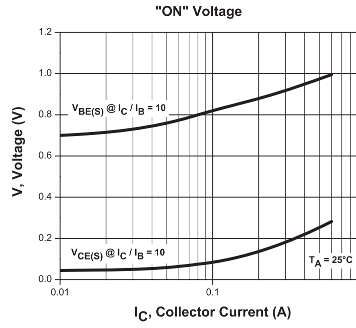
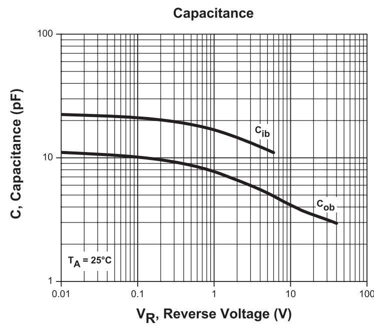
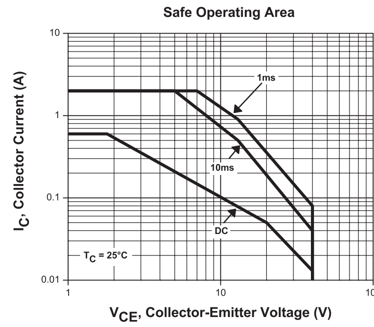
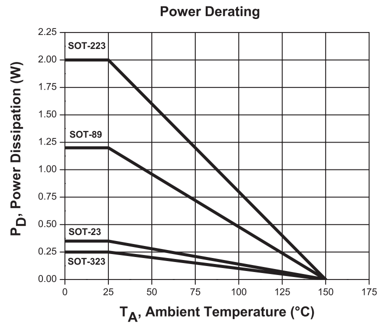
Typical Electrical Characteristics

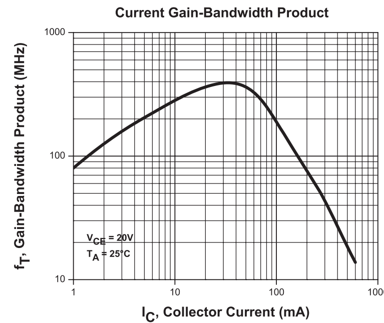












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